

## Sources of Spin Currents

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<http://nanodevices.icn2.cat>

ESM  
Cluj, Romania, Sept 2, 2015

## Spin Currents

An overview

- Spin current introduction
- Spin angular momentum current sources
  - Ferromagnetic materials (electric and thermal driving)
  - Optical orientation
  - Spin-orbit effects
  - Topological insulators
  - Mechanical motion
  - .....
- Implementations
- Nature of spin currents

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## Spin currents vs. charge currents

Basic concepts

### Charge conservation law

Charge  $q$  in position  $\vec{r}$

$$\vec{j}_c = \frac{d}{dt}(q\vec{r}) \quad \rightarrow \quad \vec{j}_c = q\vec{v}$$

electron   Electron current

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## Spin currents vs. charge currents

Basic concepts

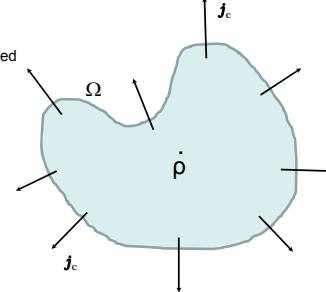
### Charge conservation law

closed surface  $\Omega$   
change in total charge enclosed

$$\iiint_V \rho dr = - \iint_{\Omega} \vec{j}_c \cdot d\Omega$$

$\rho$ : charge density  
 $\vec{j}_c$ : charge current density

Gauss theorem

$$\dot{\rho} = -\operatorname{div} \vec{j}_c$$


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## Spin currents vs. charge currents

Basic concepts

### Spin angular momentum conservation law

closed surface  $\Omega$   
change in total spin enclosed

$M$ : local magnetization  
magnetic moment density

$\vec{j}_s$ : spin current density

$$\frac{dM}{dt} = -\operatorname{div} \vec{j}_s$$

Spin angular momentum is generally not conserved

$$\frac{dM}{dt} = -\operatorname{div} \vec{j}_s + T$$

$T$ : non-conservation of angular momentum  $T = -(M - M_0)/\tau$

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## Spin currents vs. charge currents

Basic concepts

### Spin angular momentum current (second-rank tensor)

Spin  $\sigma$  in position  $\vec{r}$

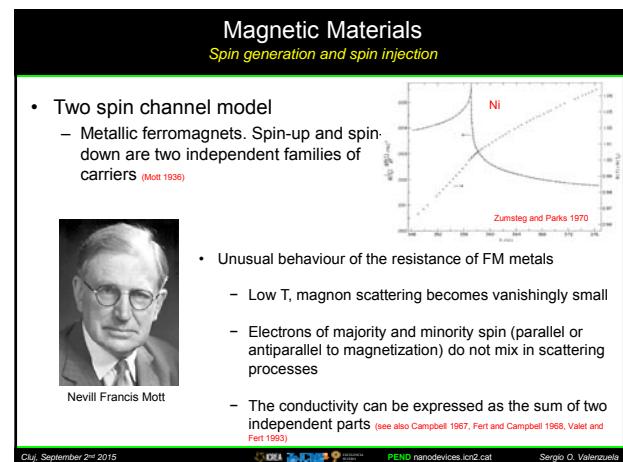
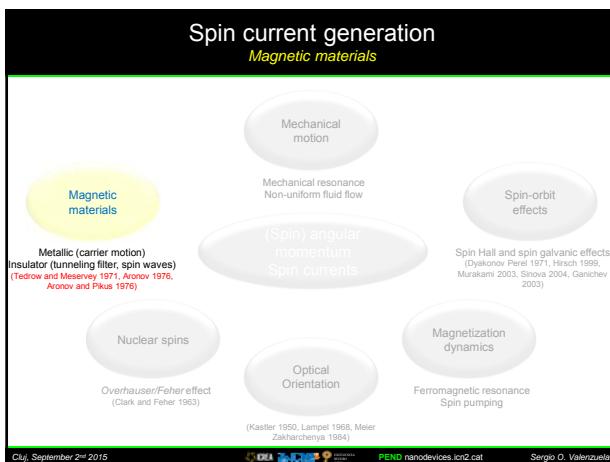
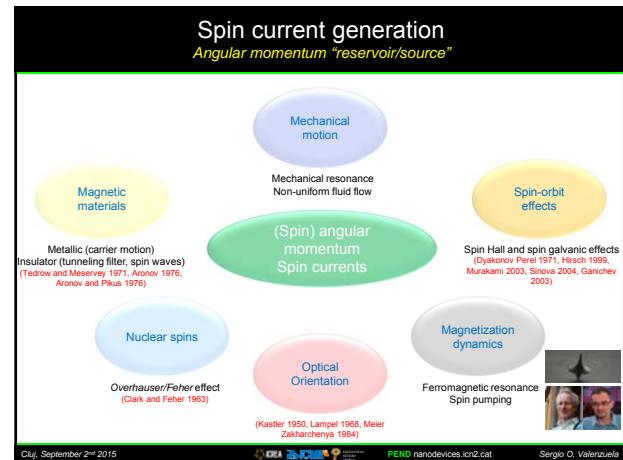
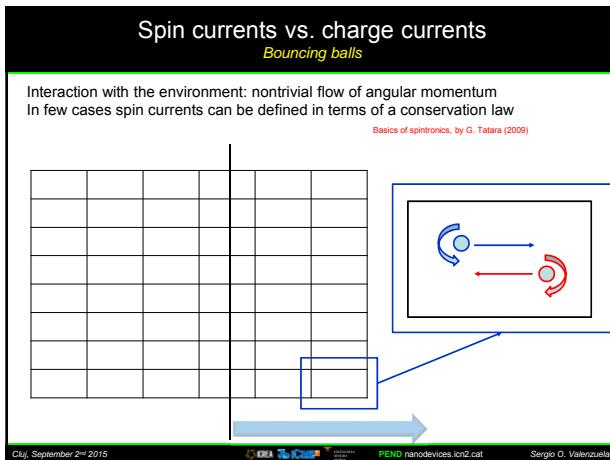
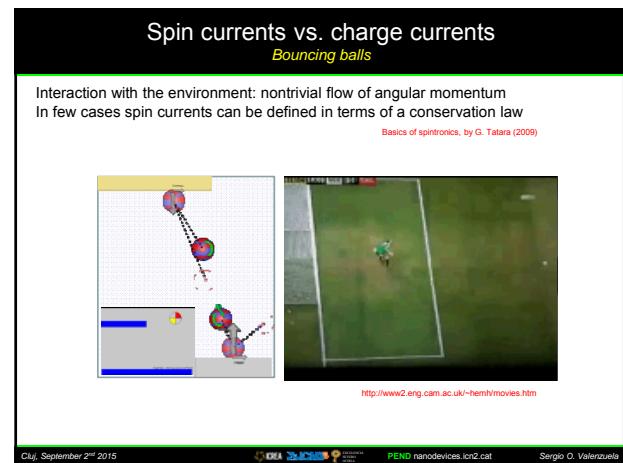
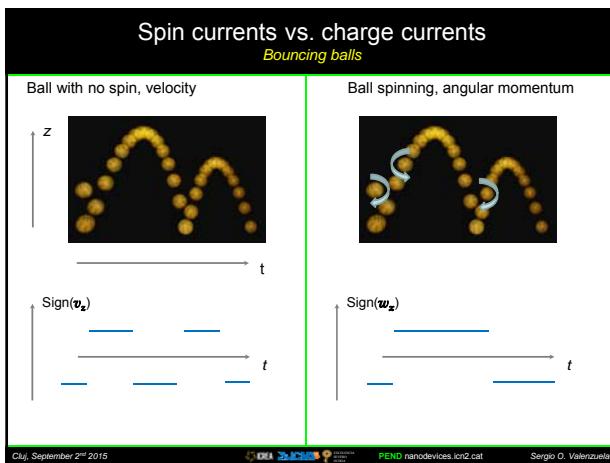
$$\vec{j}_s = \frac{d}{dt}(\sigma\vec{r}) \quad \rightarrow \quad \vec{j}_s = \boxed{\sigma} \vec{v} + \sigma \vec{r}$$

electron + spin 

Spin angular momentum current 

Costache and SOV Science 2010

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### Magnetic Materials Spin generation and spin injection

- Exchange splitting (Slater 1938)
  - Different density of states at the Fermi level for spin up and down carriers
  - Different mobility for spin up and down carriers

Different  $m^*$ ,  $v_F$ ,  $k_F(E_F)$ , thus different conductivity  $\sigma$

$$P = \frac{N_M - N_m}{N_M + N_m}$$

$$-1 \leq P \leq 1$$

Edmund Clifton Stoner

Cluj, September 2nd 2015



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### Magnetic Materials Spin generation and spin injection

- Spin polarized current in a nonmagnetic metal
- Spin accumulation decays exponentially
- Characteristic length. Spin diffusion/relaxation length  $\lambda_{sf}$

Current direction

Ferromagnet Paramagnet

$\mu$

$x(\lambda_{sf})$

F N

Johnson and Silsbee PRB 35, 4959 (1987)  
van Son et al., PRB 58, 2271 (1998)

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### Spin current outside a ferromagnet Meservey and Tedrow experiment

- Meservey-Tedrow technique. Superconductor with Zeeman split density of states as a spin detector
  - $P$  is obtained at high field, low temperatures and zero bias

Barrier

FM SC

$H$

$E_F$

$N$

$2\mu_B H / \Delta$

$eV/\Delta$

G

$H = 2-3T$

$H = 1-2T$

Partially polarized materials:  
Fe, Co, Ni  
( $P \sim 25-45\%$ )

Meservey and Tedrow, PRL 1971, Review: Phys. Rep. 238, 173 (1994)

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### Spin current outside a ferromagnet Meservey and Tedrow experiment

Ni

Co(II)

Fe(II)

POLARIZATION (%)

H (kOe)

Fe

Ni

Co

Meservey and Tedrow, PRB 1973

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### Spin current outside a ferromagnet Meservey and Tedrow experiment

Al

CoFe

NiFe

$V$

$I$

$R$

$P$  (%)

$dI/dV$  (arb. unit)

$V_{Al} - V_{NiFe}$  (mV)

$V_{Al} - V_{CoFe}$  (mV)

$H = 0, 2T$

SOV and M. Tinkham, APL 85, 5914 (2004)

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### Solid-state spin filter Spin tunnelling through a ferromagnetic insulator

The observation of internal field emission (Fowler-Nordheim tunneling) in magnetically ordered insulators is reported. A large magnetic field effect was observed and interpreted as a decrease in the barrier height due to spin ordering (Esaki et al. PRL 1967)

$E_{vac}$

$w_1$

$w_2$

$\Delta E_x$

$V_{Al}$

$V_{EuS}$

$V_{Bottom}$

$dI/dV$  ( $A/V^{1/2} \Omega^{-1}$ )

$V_{Al} - V_{EuS}$  (mV)

$V_{Al} - V_{Bottom}$  (mV)

$dI/dV$  ( $A/V^{1/2} \Omega^{-1}$ )

$V_{Al} - V_{Bottom}$  (mV)

Sample 4

$T = 0.49K$   $H = 0T$

Normalized Conductance

Au/EuS/AI

Al/EuS/Al

Moodera et al. PRL 1988, PRB 1990

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## Polarization

*How is it defined?*

- Spin splitting
  - Different density of states at the Fermi level for spin up and down carriers
  - Different mobility for spin up and down carriers

$$P = \frac{N_M - N_m}{N_M + N_m} \quad -1 \leq P \leq 1$$

L. I. Mazin, PRL 83, 1427-1430 (1999)

Edmund Clifton Stoner

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## Polarization

*How is it defined?*

$$P = \frac{N_M - N_m}{N_M + N_m} \quad \text{Fraction of unpaired carriers: ratio of spin current to charge current.}$$

$$P = \frac{j_s / \mu_B}{j_c / e}$$

The polarization is not unequivocally defined for each ferromagnet, it depends on the experimental details and measurement method. I. I. Mazin, PRL 83, 1427-1430 (1999)

- From energy band calculations  $P < 0$  for Ni and  $P > 0$  for Fe
- Experimentally TMR  $> 0$  for Ni-Fe and bias dependent
- Tunneling probability has to be taken into account (tunneling matrix)
- Current and tunneling mediated by free(s)-like electrons (s-electrons are more extended and move easily)
- Interface. Symmetry states

Sterns, J. Magn. Magn. Mat. 5, 167 (1977)

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## Polarization

*How is it defined?*

Tunnelling conductance depends strongly on the symmetry of the Bloch states in the electrodes and of the evanescent states in the barrier layer. Buttler et al PRB (2000)

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## Polarization

*How is it defined?*

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**Photoemission experiments:**  
Density of states  $P = \frac{g(E_F)_\uparrow - g(E_F)_\downarrow}{g(E_F)_\uparrow + g(E_F)_\downarrow}$

**Tunnelling Transport:**  
Matrix elements  $P = \frac{g(E_F)_\uparrow |T_\uparrow|^2 - g(E_F)_\downarrow |T_\downarrow|^2}{g(E_F)_\uparrow |T_\uparrow|^2 + g(E_F)_\downarrow |T_\downarrow|^2}$

**Ballistic transport:**  
Weight with the Fermi velocity  $P = \frac{g(E_F)_\uparrow v_{F\uparrow}^2 t_\uparrow - g(E_F)_\downarrow v_{F\downarrow}^2 t_\downarrow}{g(E_F)_\uparrow v_{F\uparrow}^2 t_\uparrow + g(E_F)_\downarrow v_{F\downarrow}^2 t_\downarrow}$

**Diffusive transport:**  
Weight with the Fermi velocity squared  $P = \frac{g(E_F)_\uparrow v_{F\uparrow}^2 t_\uparrow^2 - g(E_F)_\downarrow v_{F\downarrow}^2 t_\downarrow^2}{g(E_F)_\uparrow v_{F\uparrow}^2 t_\uparrow^2 + g(E_F)_\downarrow v_{F\downarrow}^2 t_\downarrow^2}$

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## Spintronics

*Spin generation and spin injection*

- Spin polarized current in a nonmagnetic metal
- Spin accumulation decays exponentially
- Characteristic length. Spin diffusion/relaxation length  $\lambda_{sf}$

Johnson and Slade PRB 35, 4989 (1987)  
van Son et al., PRL 58, 2271 (1987)

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## Spintronics

*Two-terminal spintronics. Giant Magnetoresistance (GMR)*

Parallel Magnetization,  $\uparrow\uparrow$   
High conductance

Antiparallel Magnetization,  $\uparrow\downarrow$   
Low conductance

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## Spintronics

*Two-terminal spintronics. Giant Magnetoresistance (GMR)*

Nobel Prize 2007

United States Patent [1] Patent Number: 4,949,039  
Greisberg  
[54] MAGNETIC FIELD SENSOR WITH PERMANENT MAGNETIC THIN LAYERS HAVING MAGNETICALLY ANTI-PARALLEL POLARIZED COMPONENTS  
[62] U.S. Prior Art Citations  
[56] Reference Cited  
[73] Inventor: Peter Grünberg, Jülich, Fed. Rep. of Germany  
[75] Assignee: IBM Corp., White Plains, NY, USA  
[85] Application Data  
[36] Filed: Aug. 14, 1990  
[37] Priority: Aug. 14, 1990  
[38] Publication Date: May 1, 1990  
[39] Patent Type: Utility Patent  
[40] Number of Claims: 1  
[41] Drawing: 1  
[42] Description: A magnetic field sensor having two permanent magnet layers, each having a ferromagnetic thin layer having magnetically anti-parallel polarized components. The sensor is used in a hard disk drive.

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## Spintronics

*Two-terminal spintronics. Tunnel Magnetoresistance (TMR)*

High G      Low G

$G_p \approx N_M^L N_M^R + N_m^L N_m^R$

$G_{AP} \approx N_M^L N_m^R + N_m^L N_M^R$

Julliere (1975); Moodera et al (1995); Miyazaki and Tezuka (1995)

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## Spin valves (Current technology)

*Giant magnetoresistance (GMR), Tunnel Magnetoresistance (TMR)*

Magnetic field sensors/data storage

Tunneling magnetoresistance

Legend: Underlays, Seed layer, Magnetic free layer, Tunnel barrier layer, Ru spacer layer, Magnetic pinned layer, Anti-ferromagnetic exchange bias layer.

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## Spintronics

*Today. Magnetic junctions and MRAM*

Instantaneous "on" of electronic devices

Smaller and faster portable equipment, e.g. cell phones, tablets, MP3 players, etc.

MagRAM Architecture

Reading a bit

Writing "1"

Writing "0"

MTJ MagRAM promises:

- density of DRAM
- speed of SRAM
- non-volatility

http://www.research.ibm.com

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## How to characterize spin transport properties?

*Nonlocal spin electronics*

The measured voltage depends on the relative magnetization of the ferromagnets

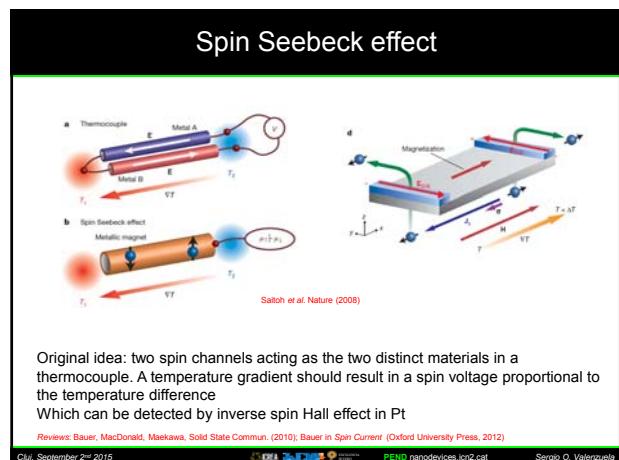
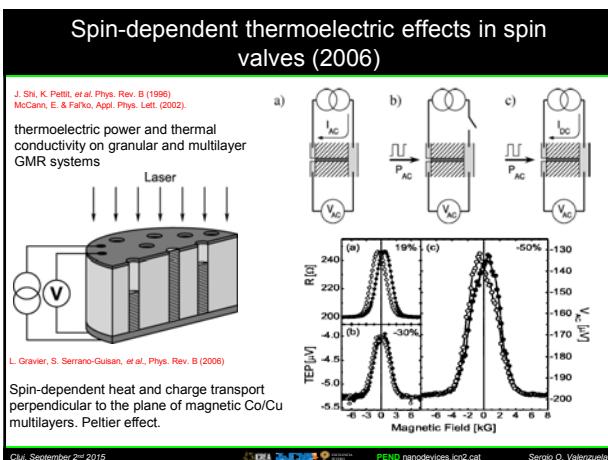
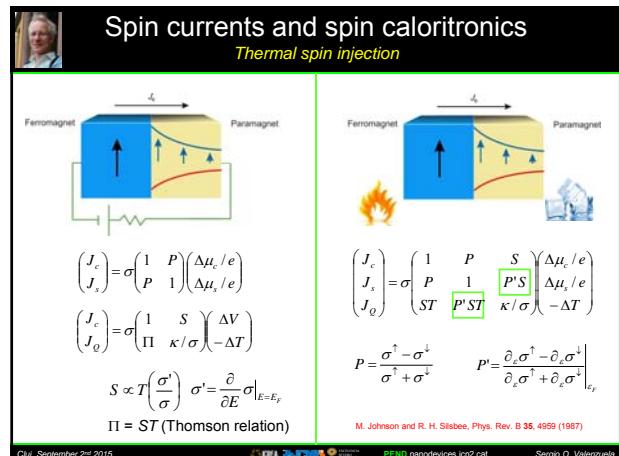
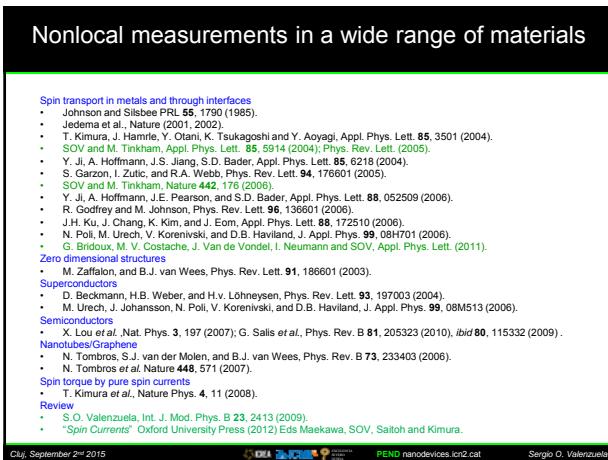
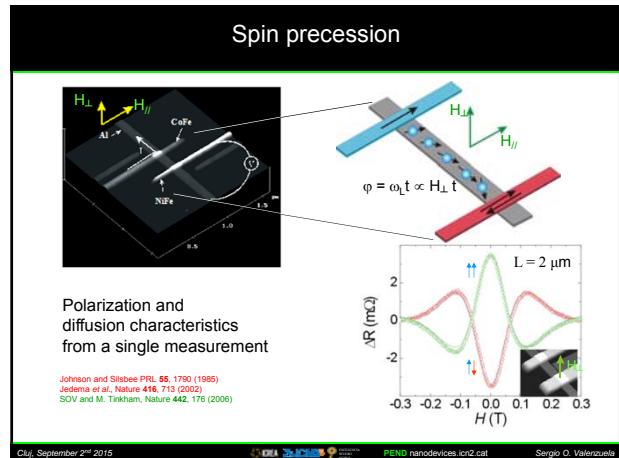
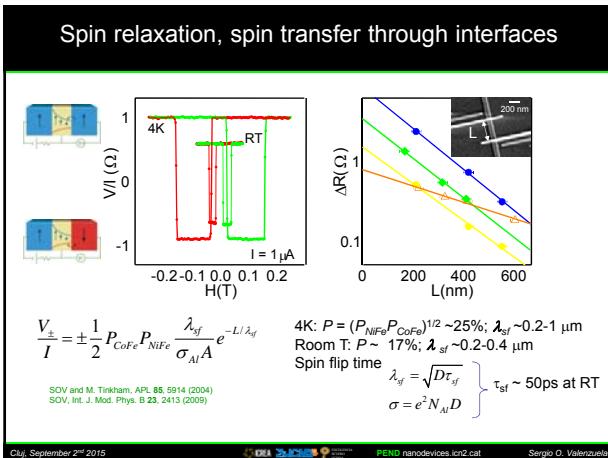
Johnson and Sisbee (1985); Aronov (1976)

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## Measurement scheme

- Current  $I$  injected into Al strip from one of the ferromagnets (CoFe)
- Non-equilibrium spin density (spin accumulation)
- The detector (NiFe) samples the electrochemical potential of the spin populations
- $L$  is varied to obtain the spin relaxation length

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## Spin Seebeck effect Basic mechanism

**Spin Seebeck in insulators**

**Magnon T ≠ Electron-phonon T**

**Spin pumping (SP) vs. Johnson-Nyquist noise**

$$V_{ISHE} \propto J_S$$

$$J_S = J_S^{SP} - J_S^{J-N} = C(T_F^M - T_N^e)$$

**Uchida et al. Nature Mater. (2010); Xiao et al. Phys. Rev. B (2010); Bauer et al. Nature Mater. (2012)**

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## Spin-dependent Seebeck effect

**a)** Schematic of a spin-dependent Seebeck effect device with a ferromagnetic metal M on a non-magnetic insulator IM.

**b)** Plot of  $R_S$  (mV/mA) vs.  $I$  (mA) showing a negative differential resistance at low currents.

**c)** Plot of  $R_S$  (μV/mT) vs. Magnetic Field (mT) showing oscillatory behavior.

**Slachter et al. Nature Phys. (2010)**

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## Nonlocal measurements in a wide range of materials

**Spin transport in metals and through interfaces**

- Johnson and Silsbee PRL **59**, 1750 (1985).
- Jedema et al. Nature (2001-2003).
- T. Kimura, J. Hanrile, Y. Otani, N. Tsukagoshi and Y. Aoyagi, Appl. Phys. Lett. **85**, 3501 (2004).
- SOV and M. Tinkham, Appl. Phys. Lett. **85**, 5914 (2004); Phys. Rev. Lett. (2005).
- Y. Ji, A. Hoffmann, J.S. Jiang, S.D. Bader, Appl. Phys. Lett. **85**, 6218 (2004).
- S. Garzon, I. Zutic, and R.A. Webb, Phys. Rev. Lett. **94**, 176601 (2005).
- SOV and M. Tinkham, Nature **442**, 176 (2006).
- Y. Ji, A. Hoffmann, and S.D. Bader, Appl. Phys. Lett. **88**, 052509 (2006).
- R. Goennenwein and M. Johnsson, Phys. Rev. Lett. **95**, 136601 (2005).
- J.H. Ku, J. Chang, K. Kim, and J. Eom, Appl. Phys. Lett. **88**, 172510 (2006).
- N. Poli, M. Urech, V. Korenivski, and D.B. Haviland, J. Appl. Phys. **99**, 084701 (2006).
- G. Bridoux, M. V. Costache, J. Van de Vondel, I. Neumann and SOV, Appl. Phys. Lett. (2011).

**Zero dimensional structures**

- M. Zaffalon, and B.J. van Wees, Phys. Rev. Lett. **91**, 186601 (2003).

**Superconductors**

- D. J. Scalapino, H.B. Weber, and H.v. Löhneysen, Phys. Rev. Lett. **93**, 197003 (2004).
- M. Urech, J. Johansson, N. Poli, V. Korenivski, and D.B. Haviland, J. Appl. Phys. **99**, 08M513 (2006).

**Semiconductors**

- X. Lou et al., Nat. Phys. **3**, 197 (2007); G. Salis et al., Phys. Rev. B **81**, 205323 (2010), ibid **80**, 115332 (2009).
- Nanotubes/Graphene
- N. Tombros et al. Nature **448**, 571 (2007).

**Spin torque by spin currents**

- T. Kimura et al., Nature Phys. **4**, 11 (2008).

**Reviews**

- S.O. Valenzuela, Int. J. Mod. Phys. B **23**, 2413 (2009).
- "Spin Currents" Oxford University Press (2012) Eds Maekawa, SOV, Saitoh and Kimura.

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## Spin current generation Optical orientation

**Mechanical motion**

**Magnetic materials**

**(Spin) angular momentum**

**Spin currents**

**Mechanical resonance**

**Non-uniform fluid flow**

**Spin-orbit effects**

**Metallic (carrier motion)**

**Insulator (tunneling filter, spin waves)**

**Tedrow and Meissner 1971, Aronov 1976, Aronov and Pikus 1976**

**Nuclear spins**

**Overhauser/Feher effect**

**(Clark and Feher 1963)**

**Optical Orientation**

**Kastler 1950, Lampel 1968, Meier Zaharkenya 1984**

**Magnetization dynamics**

**Ferromagnetic resonance**

**Spin pumping**

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## Conductance mismatch Fundamental obstacle spin injection into a semiconductor

The difference in electrochemical potential between spin-up and spin-down collapses within the spin relaxation length

The resistance contributing to the splitting of the potentials

$$R_{fm}^{\uparrow\downarrow} = \frac{2\lambda}{\sigma_{fm}(1 \pm \beta)}$$

Here  $\beta$  is the spin polarization ( $P$ ) of the ferromagnet

**Solutions:**

- 1- add a high resistance in spin channels with a strong spin asymmetry
- 2- Use semiconducting FMs

Schmidt et al 2000, 2005

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## Optical orientation/pumping Spin injection by optical methods

**Conservation of angular momentum**

Photons of right or left polarized light have a projection of the angular momentum on the direction of their propagation (helicity) equal to +1 or -1, respectively (in units of  $\hbar$ )

Electron orbital momentum is oriented by light and through spin-orbit interaction electron spins become polarized

For the simple case of an atom/molecule

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### Optical orientation/pumping Spin injection by optical methods

Circularly polarized photon absorbed in a semiconductor

Angular momentum distributed between the photo-excited electron and hole according to the selection rules determined by the band structure

$E_g < \hbar\omega < E_g + \Delta$

average electron spin equal to  $(-1/2)(3/4) + (+1/2)(1/4) = -1/4$   
average hole spin equal to  $+5/4$ , with a sum +1

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### Optical orientation/pumping Spin injection by optical methods

Circularly polarized photon absorbed in a semiconductor

Angular momentum distributed between the photo-excited electron and hole according to the selection rules determined by the band structure

First report in Si

FIG. 1. Curve a: Signal proportional to the  $\text{Si}^{29}$  magnetization obtained in  $H_z=1$  G after 21 h of irradiation with circularly polarized light at 77K. Curve b: Signal proportional to the equilibrium  $\text{Si}^{29}$  magnetization in  $H_z=6$  kG at 300 °K.

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### Optical orientation/pumping Spin injection by optical methods

Circularly polarized photon absorbed in a semiconductor

Angular momentum distributed between the photo-excited electron and hole according to the selection rules determined by the band structure

Dependence on doping concentration

Kikkawa and Awschalom 1998  
Detection: Faraday Rotation

Electrical control of spin precession

Sala et al 2001

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### Spin current generation Spin Hall effects

Mechanical motion  
Magnetic materials  
(Spin) angular momentum Spin currents  
Nuclear spins  
Optical Orientation  
Spin-orbit effects

Metallic (carrier motion)  
Insulator (tunneling filter, spin waves)  
(Tedrow and Meesey 1971, Aronov 1976, Aronov and Pikus 1976)

Overhauser/Feher effect  
(Clark and Feher 1963)

Ferromagnetic resonance  
Spin pumping

Dyakonov/Purcell 1971, Hirsch 1999, Murakami 2003, Sinova 2004, Ganichev 2003

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### Spin Hall Effects Pure spin currents

The spin Hall effect has the symmetry of the conventional Hall effect

M.I. Dyakonov & V.I. Perel, JETP Lett. **13**, 467 (1971); J.E. Hirsch, PRL **83**, 1834 (1999); S. Zhang, PRL **85**, 393 (2000); S. Murakami, N. Nagaosa, S.C. & Zhang, Science **301**, 1348 (2003); J. Sinova, et al., PRL **92**, 126603 (2004).

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### Spin Hall Effects Pure spin currents

Scattering of unpolarized electrons by an unpolarized target results in spatial separation of electrons with different spins due to spin-orbit interaction

N. F. Mott and H. S. W. Massey, *The theory of atomic collisions* (Clarendon Press, Oxford, 1965)

Anomalous Hall effect (1881)  
E.H. Hall, Phil. Mag. **12**, 157 (1881)

M.I. Dyakonov & V.I. Perel, JETP Lett. **13**, 467 (1971); J.E. Hirsch, PRL **83**, 1834 (1999)

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